



60V NPN LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

- BV_{CEO} > 60V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- I_C = 6A high Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 60mV @ 1A
- hFE Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: DXTP03060CFG
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.03 grams (Approximate)

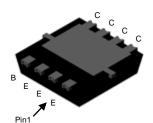
Applications

- MOSFET & IGBT Gate Drivers
- Solenoid, Relay and Actuator Drivers
- DC to DC Converters
- Motor Control

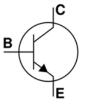
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



Device Symbol

Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTN03060CFG-7	Standard	2J4	7	12	2,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



2J4 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 21 = 2021)

WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	100	V
Collector-Emitter Voltage	Vceo	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	6	А
Peak Pulse Current	Ісм	20	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Dower Dissination	(Note 5)	D-	1.2	
Power Dissipation	(Note 6)	PD	2.7	W
Thermal Resistance, Junction to Ambient	(Note 5)	D	107	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	− R _{θJA}	48	°C/W
Thermal Resistance, Junction to Leads (Note 7	ReJL	8.5	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

ESD Ratings (Note 8)

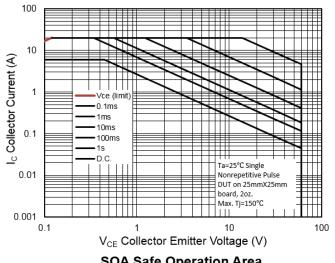
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

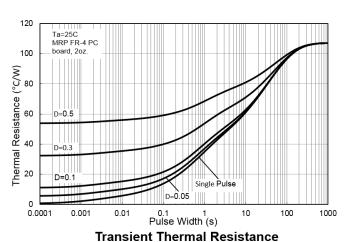
Notes:

- 5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the collector tab). 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

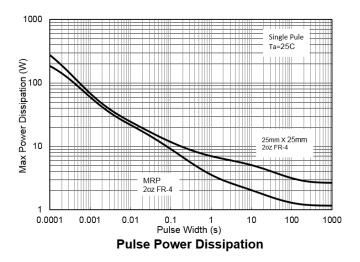


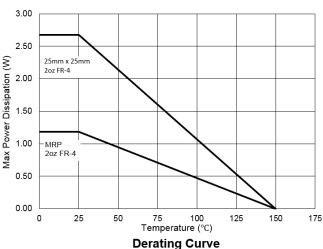
Thermal Characteristics and Derating Information





SOA Safe Operation Area







Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

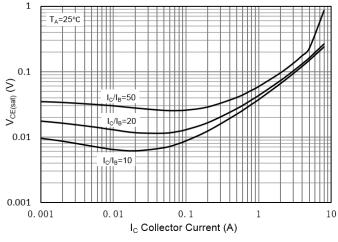
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	100	201	_	V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BVceo	60	78	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.9	_	V	I _E = 100μA
Collector Cut-off Current	Ісво	_	3	50	nA	V _{CB} = 100V
Conector Cut-on Current		_	0.2	10	μΑ	V _{CB} = 100V, T _A = +125°C
Collector Cut-off Current	ICER	_	8	50	nA	V _{CB} = 80V
Conector Cut-on Current	$R_B \le 1k\Omega$	_	0.3	10	μΑ	V _{CB} = 80V, T _A = +125°C
Emitter Cut-off Current	I _{EBO}	_	1	20	nA	V _{EB} = 6V
		200	354	_	_	Ic = 10mA, VcE = 2V
		200	357	_	_	Ic = 100mA, VcE = 2V
DC Current Gain (Note 9)	h _{FE}	200	343	800	_	$I_C = 1A$, $V_{CE} = 2V$
		200	325	_	_	Ic = 2A, VcE = 2V
		75	133		_	Ic = 5A, VcE = 2V
	VCE(sat)	_	13	30	mV	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
		_	37	60	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 9)		_	43	70	mV	Ic = 1A, I _B = 50mA
		_	88	135	mV	Ic = 2A, I _B = 50mA
		_	194	260	mV	$I_C = 6A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE} (sat)	_	1000	1100	mV	Ic = 6A, I _B = 300mA
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	930	1050	mV	Ic = 6A, VcE = 1V
Input Capacitance	Cibo	_	509	_	pF	V _{EB} = 0.5V. f = 1MHz
Output Capacitance	C _{obo}	_	290	_	pF	V _{CB} = 10V. f = 1MHz
Current Gain-Bandwidth Product	ft	_	140	_	MHz	V _{CE} = 5V, I _C = 100mA, f = 100MHz
	t _{delay}	_	16.5	_	ns	
Switching Time	trise	_	5.8	_	ns	$I_C = 1A, V_{CC} = 10V,$
Switching riffle	t _{storage}	_	1273	_	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$
	t _{fall}	_	27.5	_	ns	

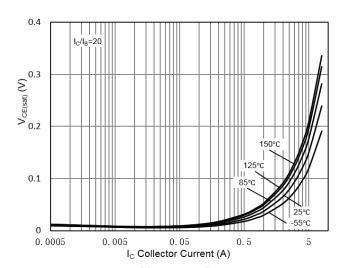
Note:

9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

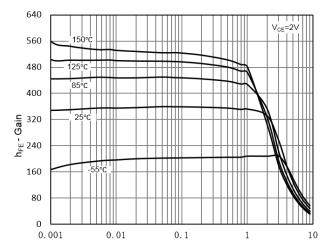


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

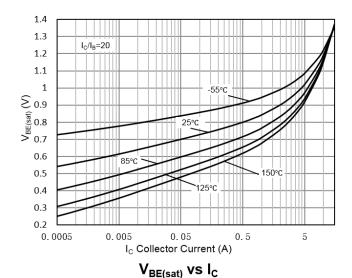




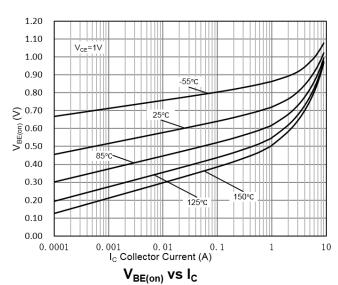




 $V_{\text{CE(sat)}} vs I_{\text{C}}$



 I_C Collector Current (A) h_{FE} VS I_C



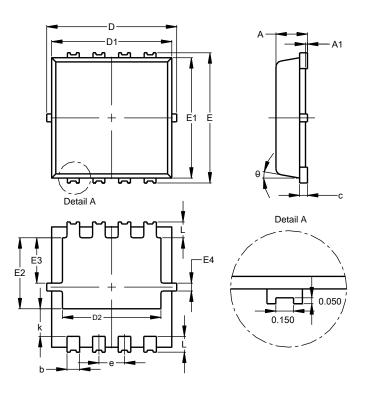
180 160 140 (MHz) 100 80 60 40 20 0 50 60 Ic (mA) 10 20 30 40 70 80 90 100 fT v lc



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

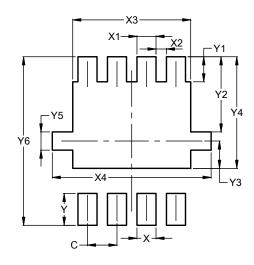


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Χ	0.420			
X1	0.420			
X2	0.230			
Х3	2.600			
X4	3.500			
Υ	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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